

November 2013

FDP61N20

N-Channel UniFETTM MOSFET 200 V, 61 A, 41 m Ω

Features

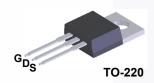
- $R_{DS(on)}$ = 34 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 30.5 A
- Low Gate Charge (Typ. 58 nC)
- Low C_{rss} (Typ. 80 pF)
- · 100% Avalanche Tested

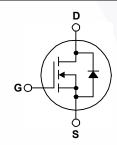
Applications

- PDP TV
- Lighting
- · Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FDP61N20	Unit
V _{DSS}	Drain-Source Voltage		200	V	
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)		61 38.5	A A	
I _{DM}	Drain Current	- Pulsed	(Note 1)	244	Α
V _{GSS}	Gate-Source voltage		±30	V	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		1440	mJ	
I _{AR}	Avalanche Current (No		(Note 1)	61	Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		(Note 1)	41.7	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns	
P _D	Power Dissipation	(T _C = 25°C) - Derate Above 25°C		417 3.3	W W/°C
T _{J,} T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C

Thermal Characteristics

Symbol	Parameter	FDP61N20	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	C/VV

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP61N20	FDP61N20	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics			•	•	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA				V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.2		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 200 V, V _{GS} = 0 V V _{DS} = 160 V, T _C = 125°C			1 10	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 30.5 A		0.034	0.041	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 30.5 A		44.5		S
Dynamic C	Characteristics					
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		2615	3380	pF
C _{oss}	Output Capacitance			645	840	pF
C _{rss}	Reverse Transfer Capacitance			80	120	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 100 V, I _D = 61 A,		40	90	ns
t _r	Turn-On Rise Time	V_{GS} = 10 V, R_G = 25 Ω		215	440	ns
t _{d(off)}	Turn-Off Delay Time	(Note 4)		125	260	ns
t _f	Turn-Off Fall Time			170	350	ns
Qg	Total Gate Charge	V _{DS} = 160 V, I _D = 61 A,		58	75	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		19		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		24		nC
Drain-Soul	rce Diode Characteristics and Maximun	n Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				61	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				244	Α
V_{SD}	Drain-Source Diode Forward Voltage V _{GS} = 0 V, I _S = 61 A				1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 61 A,		162		ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt =100 A/μs		1.5		μС

Notes

^{1.} Repetitive rating: pulse-width limited by maximum junction temperature.

^{2.} L = 0.58 mH, I $_{AS}$ = 61 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 $\Omega,$ starting T $_{J}$ = 25 $^{\circ}C.$

^{3.} I $_{SD}$ \leq 61 A, di/dt \leq 200 A/µs, V $_{DD}$ \leq BV $_{DSS}$, starting T $_{J}$ = 25°C.

^{4.} Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

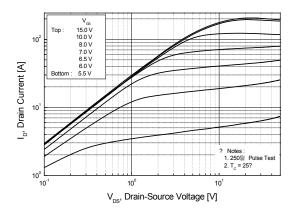


Figure 2. Transfer Characteristics

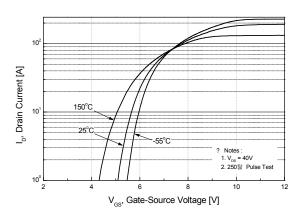
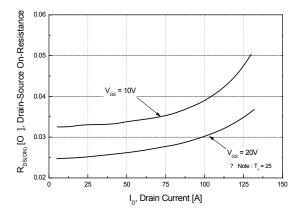


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage





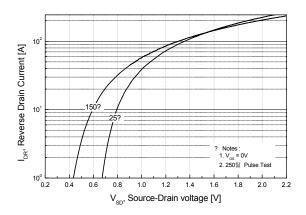


Figure 5. Capacitance Characteristics

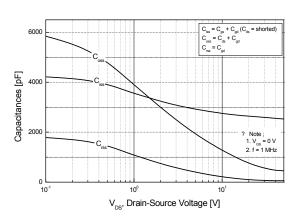
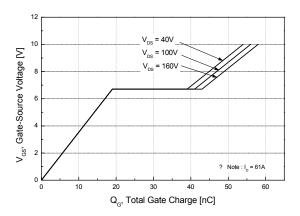


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

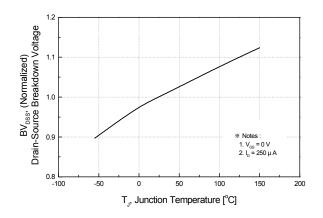


Figure 8. On-Resistance Variation vs. Temperature

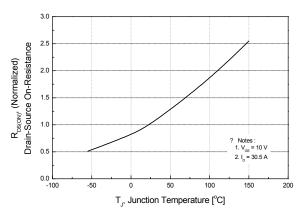


Figure 9. Safe Operating Area

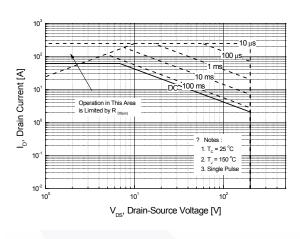


Figure 10. Maximum Drain Current vs. Case Temperature

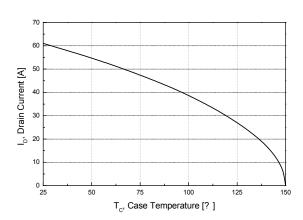
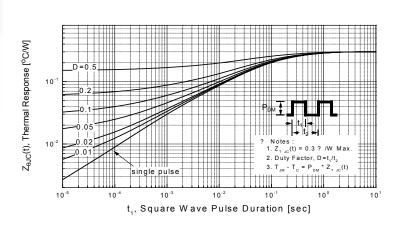


Figure 11. Transient Thermal Response Curve



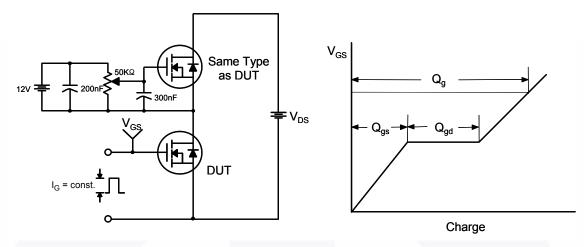


Figure 12. Gate Charge Test Circuit & Waveform

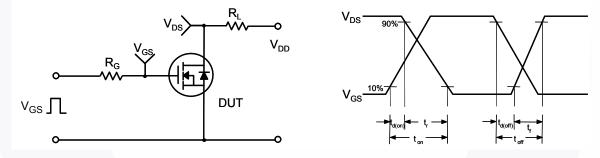


Figure 13. Resistive Switching Test Circuit & Waveforms

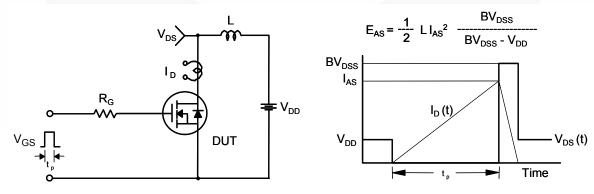


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

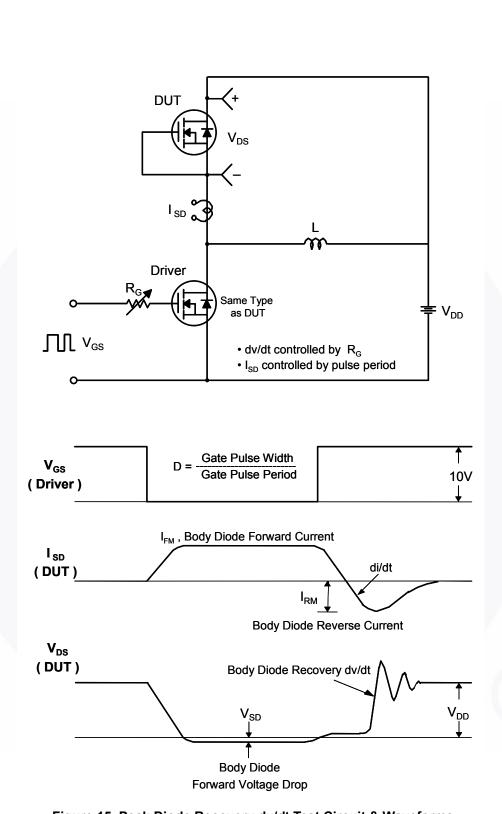


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

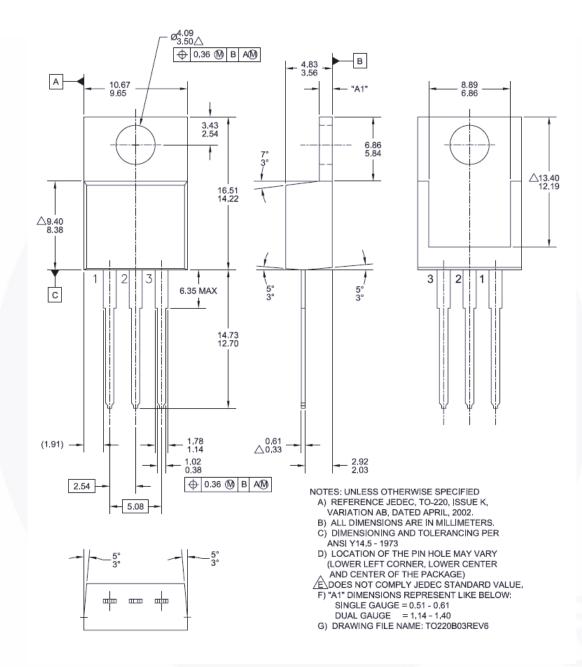


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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